METHOD OF FORMING VARIABLE OXIDE THICKNESSES ACROSS SEMICONDUCTOR CHIPS

ABSTRACT OF THE INVENTION

A method for forming variable oxide thicknesses across semiconductor chips comprises providing a silicon semiconductor substrate having pre-selected areas open to silicon surface using a photoresist layer; immersing the silicon semiconductor substrate in an HF type electrolytic bath to produce a porous silicon area; and removing the photoresist layer and oxidizing the silicon semiconductor substrate to produce a plurality of thicknesses of gate oxide on the silicon semiconductor substrate.